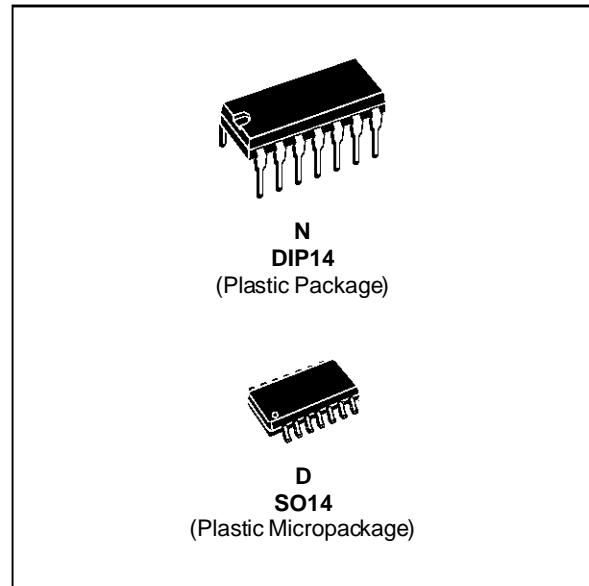


GENERAL PURPOSE
 QUAD J-FET OPERATIONAL AMPLIFIERS

- LOW POWER CONSUMPTION
- WIDE COMMON-MODE (UP TO V_{CC}^+) AND DIFFERENTIAL VOLTAGE RANGE
- LOW INPUT BIAS AND OFFSET CURRENT
- OUTPUT SHORT-CIRCUIT PROTECTION
- HIGH INPUT IMPEDANCE J-FET INPUT STAGE
- INTERNAL FREQUENCY COMPENSATION
- LATCH UP FREE OPERATION
- HIGH SLEW RATE : 16V/ μ s (typ)


DESCRIPTION

The TL084, TL084A and TL084B are high speed J-FET input quad operational amplifiers incorporating well matched, high voltage J-FET and bipolar transistors in a monolithic integrated circuit.

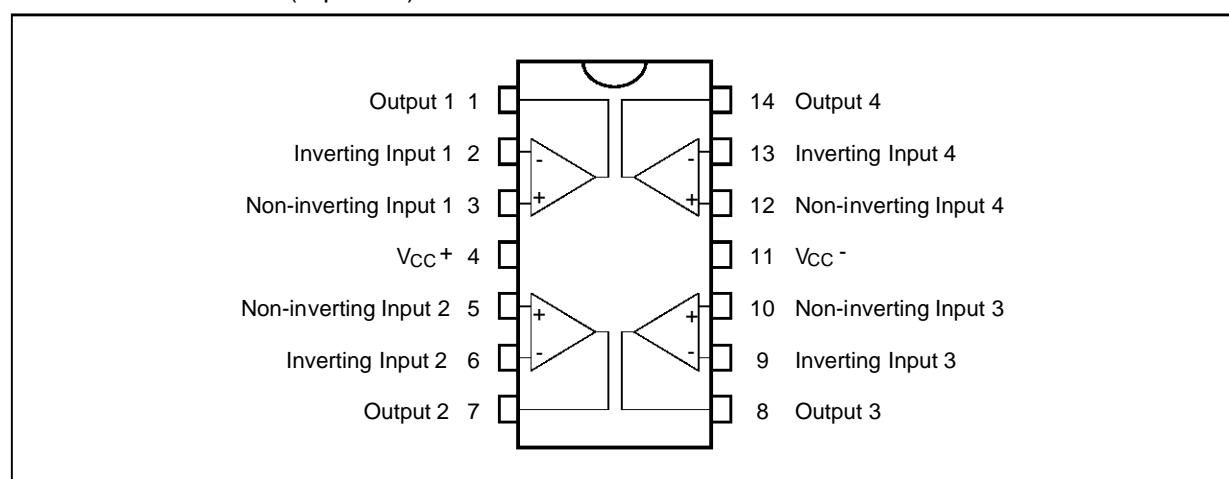
The devices feature high slew rates, low input bias and offset currents, and low offset voltage temperature coefficient.

ORDER CODES

Part Number	Temperature Range		Package	
	N	D		
TL084M/AM/BM	-55°C, +125°C		•	•
TL084I/AI/BI	-40°C, +105°C		•	•
TL084C/AC/BC	0°C, +70°C		•	•

Examples : TL084CN, TL084CD

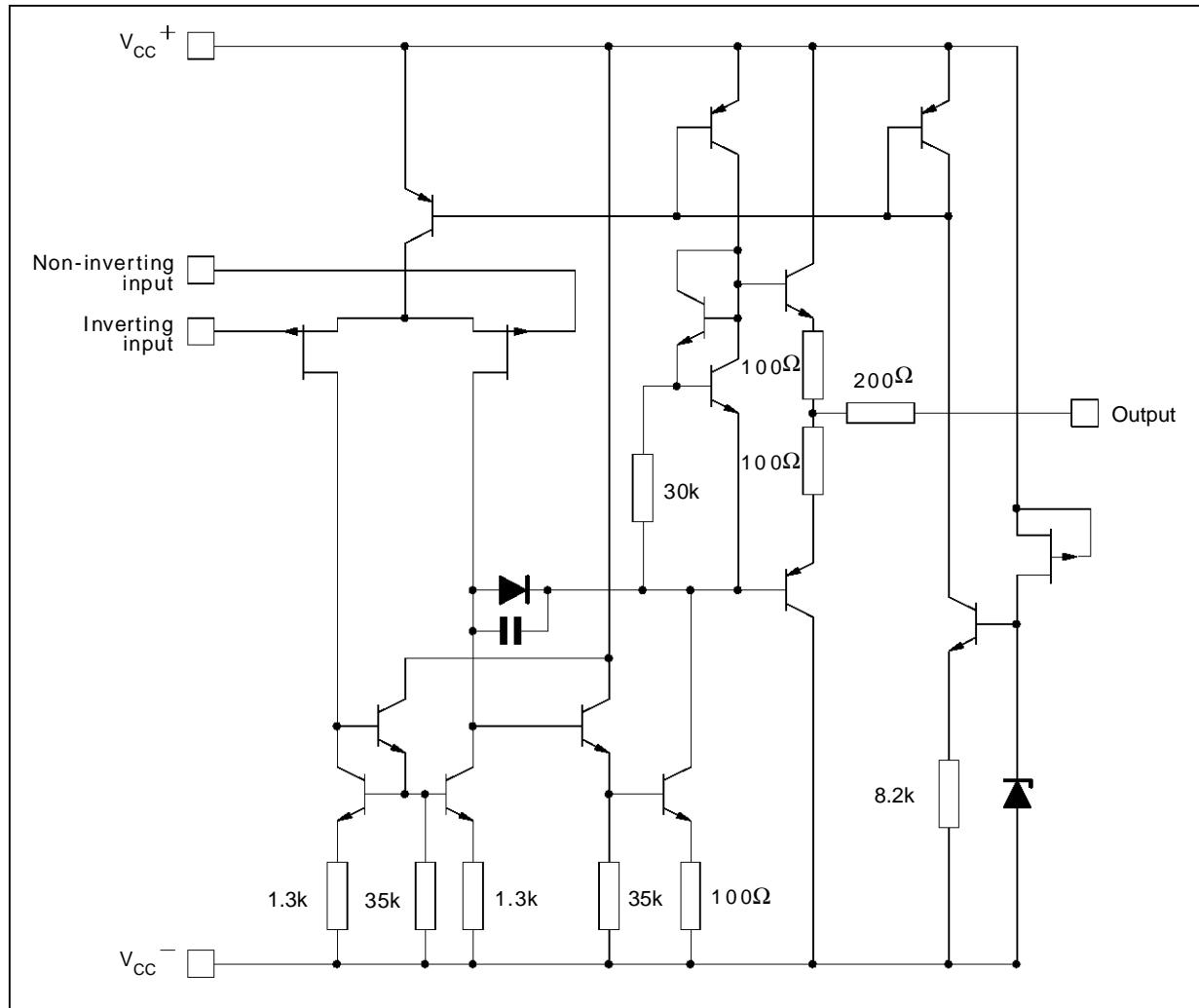
Q34-01-EP5

PIN CONNECTIONS (top view)


Q34-01-EP5

TL084 - TL084A - TL084B

SCHEMATIC DIAGRAM (each amplifier)



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{cc}	Supply Voltage - (note 1)	±18	V
V _i	Input Voltage - (note 3)	±15	V
V _{id}	Differential Input Voltage - (note 2)	±30	V
P _{tot}	Power Dissipation	680	mW
	Output Short-circuit Duration - (note 4)	Infinite	
T _{oper}	Operating Free Air Temperature Range TL084C,AC,BC TL084I,AI,BI TL084M,AM,BM	0 to 70 -40 to 105 -55 to 125	°C
T _{stg}	Storage Temperature Range	-65 to 150	°C

Notes :

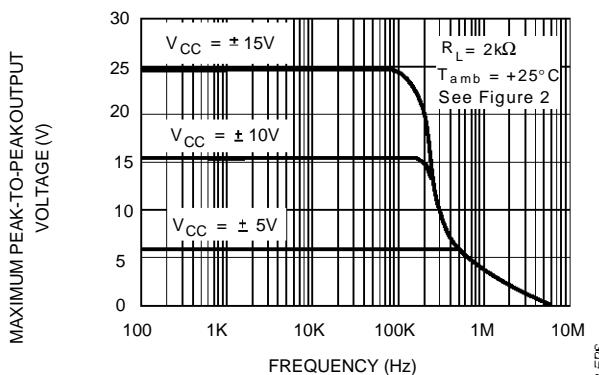
1. All voltage values, except differential voltage, are with respect to the zero reference level (ground) of the supply voltages where the zero reference level is the midpoint between V_{cc}⁺ and V_{cc}⁻.
2. Differential voltages are at the non-inverting input terminal with respect to the inverting input terminal.
3. The magnitude of the input voltage must never exceed the magnitude of the supply voltage or 15 volts, whichever is less.
4. The output may be shorted to ground or to either supply. Temperature and /or supply voltages must be limited to ensure that the dissipation rating is not exceeded.

ELECTRICAL CHARACTERISTICS $V_{CC} = \pm 15V, T_{amb} = 25^{\circ}C$ (unless otherwise specified)

Symbol	Parameter	TL084I,M,AC,AI, AM,BC,BI,BM			TL084C			Unit
		Min.	Typ.	Max.	Min.	Typ.	Max.	
V_{io}	Input Offset Voltage ($R_S = 50\Omega$) $T_{amb} = 25^{\circ}C$ $T_{min.} \leq T_{amb} \leq T_{max.}$ TL084BC,BI,BM TL084BC,BI,BM		3 1	6 3 7 5		3	10 13	mV
DV_{io}	Input Offset Voltage Drift		10			10		$\mu V/^{\circ}C$
I_{io}	Input Offset Current * $T_{amb} = 25^{\circ}C$ $T_{min.} \leq T_{amb} \leq T_{max.}$		5	100 4		5	100 4	pA nA
I_{ib}	Input Bias Current * $T_{amb} = 25^{\circ}C$ $T_{min.} \leq T_{amb} \leq T_{max.}$		20	200 20		30	400 20	pA nA
A_{vd}	Large Signal Voltage Gain ($R_L = 2k\Omega$, $V_O = \pm 10V$) $T_{amb} = 25^{\circ}C$ $T_{min.} \leq T_{amb} \leq T_{max.}$	50 25	200		25 15	200		V/mV
SVR	Supply Voltage Rejection Ratio ($R_S = 50\Omega$) $T_{amb} = 25^{\circ}C$ $T_{min.} \leq T_{amb} \leq T_{max.}$	80 80	86		70 70	86		dB
I_{cc}	Supply Current, per Amp, no Load $T_{amb} = 25^{\circ}C$ $T_{min.} \leq T_{amb} \leq T_{max.}$		1.4	2.5 2.5		1.4	2.5 2.5	mA
V_{icm}	Input Common Mode Voltage Range	± 11	+15 -12		± 11	+15 -12		V
CMR	Common Mode Rejection Ratio ($R_S = 50\Omega$) $T_{amb} = 25^{\circ}C$ $T_{min.} \leq T_{amb} \leq T_{max.}$	80 80	86		70 70	86		dB
I_{os}	Output Short-circuit Current $T_{amb} = 25^{\circ}C$ $T_{min.} \leq T_{amb} \leq T_{max.}$	10 10	40	60 60	10 10	40	60 60	mA
$\pm V_{OPP}$	Output Voltage Swing $T_{amb} = 25^{\circ}C$ $R_L = 2k\Omega$ $R_L = 10k\Omega$ $T_{min.} \leq T_{amb} \leq T_{max.}$ $R_L = 2k\Omega$ $R_L = 10k\Omega$	10 12 10 12	12 13.5		10 12 10 12	12 13.5		V
SR	Slew Rate ($V_{in} = 10V$, $R_L = 2k\Omega$, $C_L = 100pF$, $T_{amb} = 25^{\circ}C$, unity gain)	8	16		8	16		$V/\mu s$
t_r	Rise Time ($V_{in} = 20mV$, $R_L = 2k\Omega$, $C_L = 100pF$, $T_{amb} = 25^{\circ}C$, unity gain)		0.1			0.1		μs
Kov	Overshoot ($V_{in} = 20mV$, $R_L = 2k\Omega$, $C_L = 100pF$, $T_{amb} = 25^{\circ}C$, unity gain)		10			10		%
GBP	Gain Bandwidth Product ($f = 100kHz$, $T_{amb} = 25^{\circ}C$, $V_{in} = 10mV$, $R_L = 2k\Omega$, $C_L = 100pF$)	2.5	4		2.5	4		MHz
R_i	Input Resistance		10^{12}			10^{12}		Ω
THD	Total Harmonic Distortion ($f = 1kHz$, $A_V = 20dB$, $R_L = 2k\Omega$, $C_L = 100pF$, $T_{amb} = 25^{\circ}C$, $V_O = 2V_{PP}$)		0.01			0.01		%
e_n	Equivalent Input Noise Voltage ($f = 1kHz$, $R_S = 100\Omega$)		15			15		$\frac{nV}{\sqrt{Hz}}$
$\emptyset m$	Phase Margin		45			45		Degrees
V_{O1}/V_{O2}	Channel Separation ($A_V = 100$)		120			120		dB

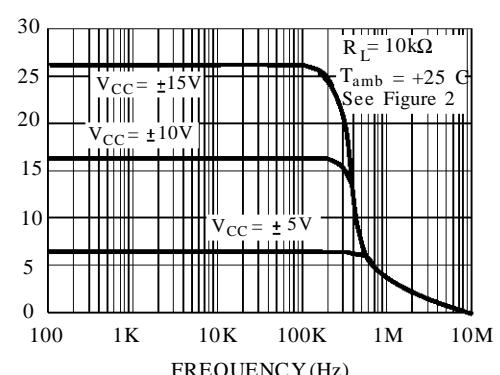
* The input bias currents are junction leakage currents which approximately double for every $10^{\circ}C$ increase in the junction temperature.

MAXIMUM PEAK-TO-PEAK OUTPUT VOLTAGE VERSUS FREQUENCY



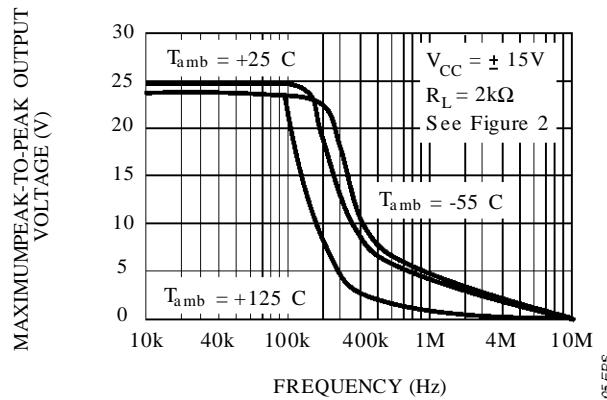
024-03.EPS

MAXIMUM PEAK-TO-PEAK OUTPUT VOLTAGE VERSUS FREQUENCY



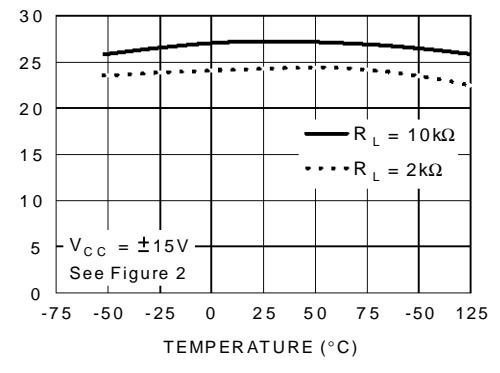
024-04.EPS

MAXIMUM PEAK-TO-PEAK OUTPUT VOLTAGE VERSUS FREQUENCY



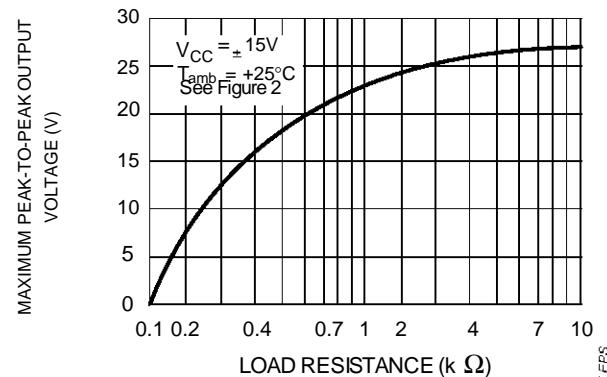
024-05.EPS

MAXIMUM PEAK-TO-PEAK OUTPUT VOLTAGE VERSUS FREE AIR TEMP.



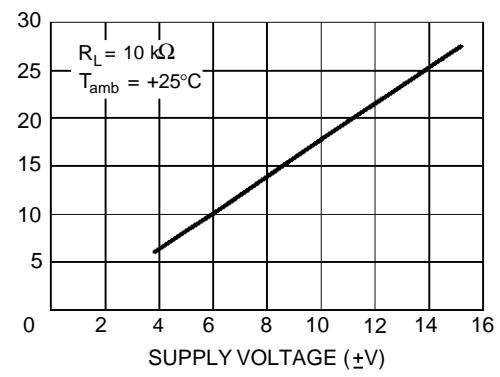
024-06.EPS

MAXIMUM PEAK-TO-PEAK OUTPUT VOLTAGE VERSUS LOAD RESISTANCE



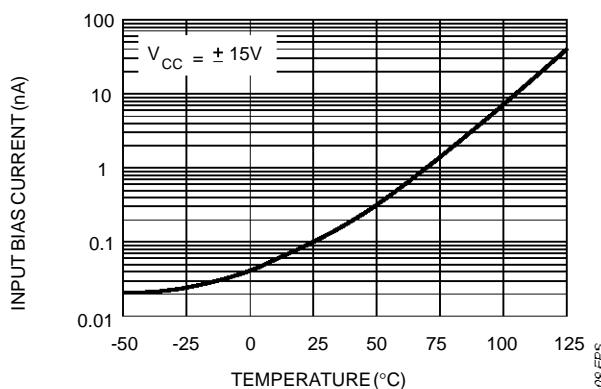
024-07.EPS

MAXIMUM PEAK-TO-PEAK OUTPUT VOLTAGE VERSUS SUPPLY VOLTAGE

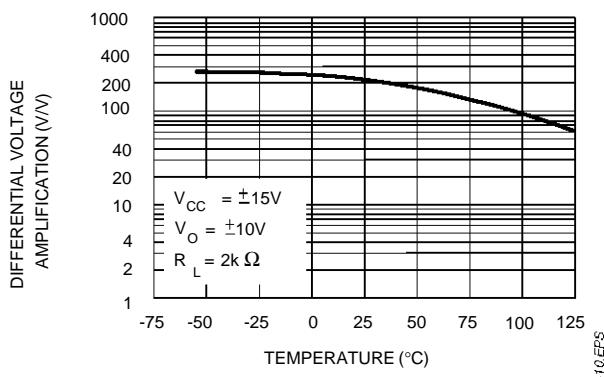


024-08.EPS

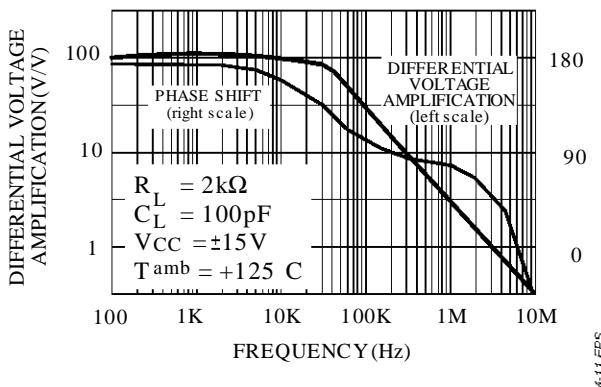
**INPUT BIAS CURRENT VERSUS
FREE AIR TEMPERATURE**



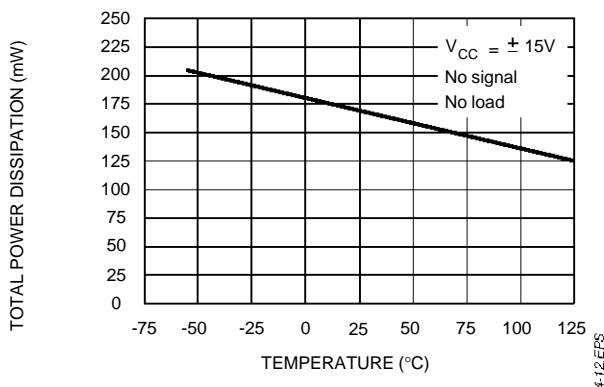
**LARGE SIGNAL DIFFERENTIAL
VOLTAGE AMPLIFICATION VERSUS
FREE AIR TEMPERATURE**



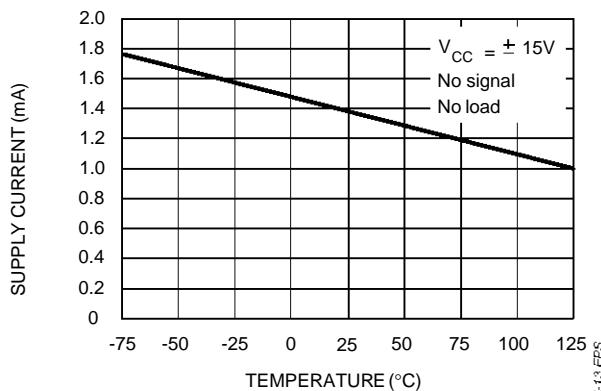
**LARGE SIGNAL DIFFERENTIAL
VOLTAGE AMPLIFICATION AND PHASE
SHIFT VERSUS FREQUENCY**



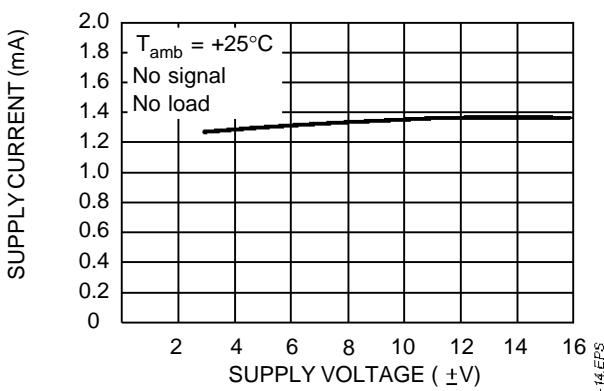
**TOTAL POWER DISSIPATION VERSUS
FREE AIR TEMPERATURE**



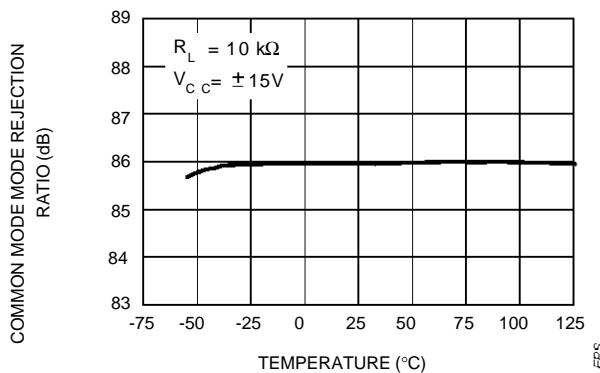
**SUPPLY CURRENT PER AMPLIFIER
VERSUS FREE AIR TEMPERATURE**



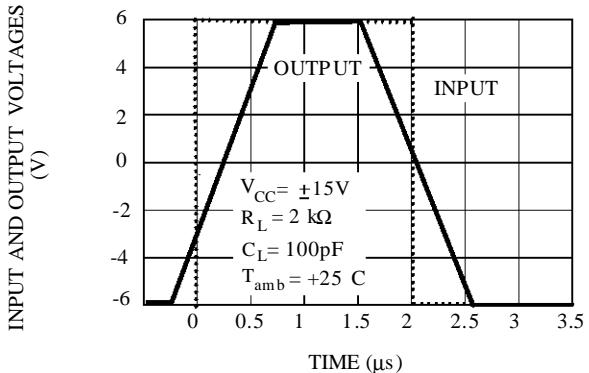
**SUPPLY CURRENT PER AMPLIFIER
VERSUS SUPPLY VOLTAGE**



**COMMON MODE REJECTION RATIO
VERSUS FREE AIR TEMPERATURE**

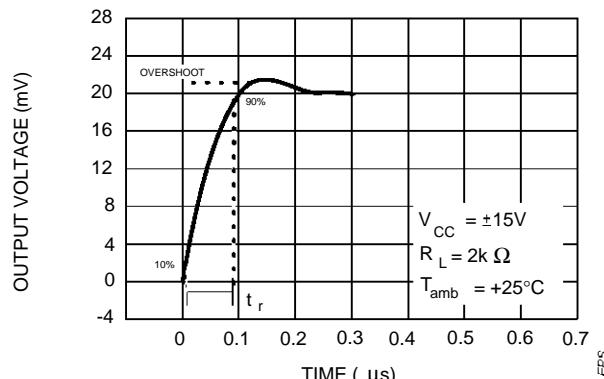


**VOLTAGE FOLLOWER LARGE SIGNAL
PULSE RESPONSE**



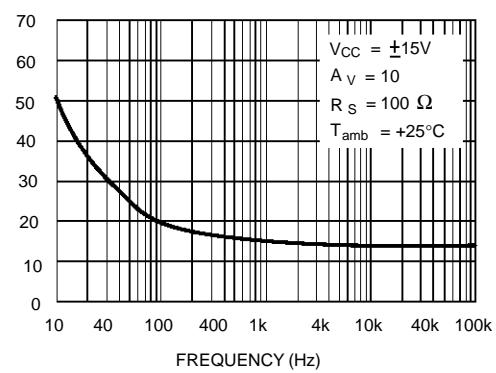
084-15.EPS

**OUTPUT VOLTAGE VERSUS
ELAPSED TIME**



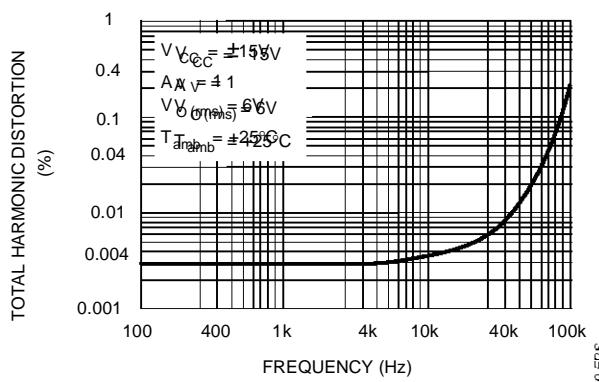
084-17.EPS

**EQUIVALENT INPUT NOISE VOLTAGE
VERSUS FREQUENCY**



084-16.EPS

**TOTAL HARMONIC DISTORTION VERSUS
FREQUENCY**



084-18.EPS

PARAMETER MEASUREMENT INFORMATION

Figure 1 : Voltage Follower

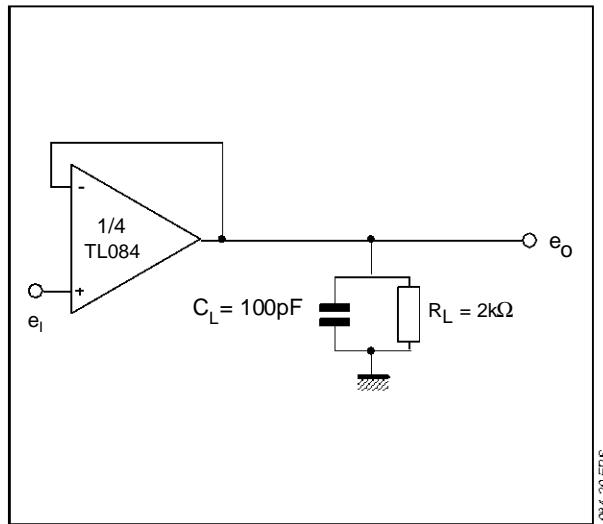
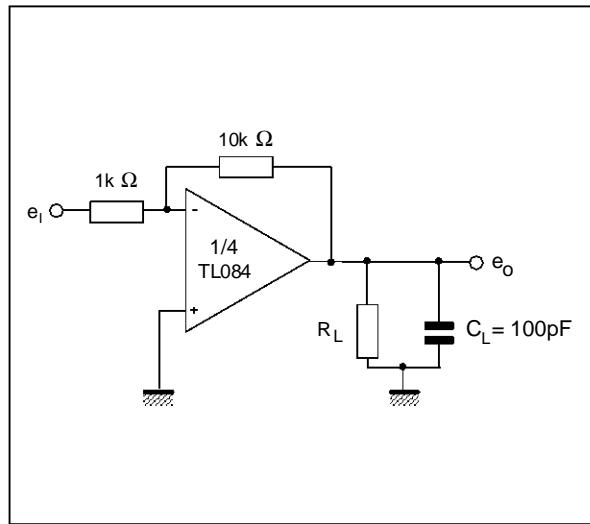
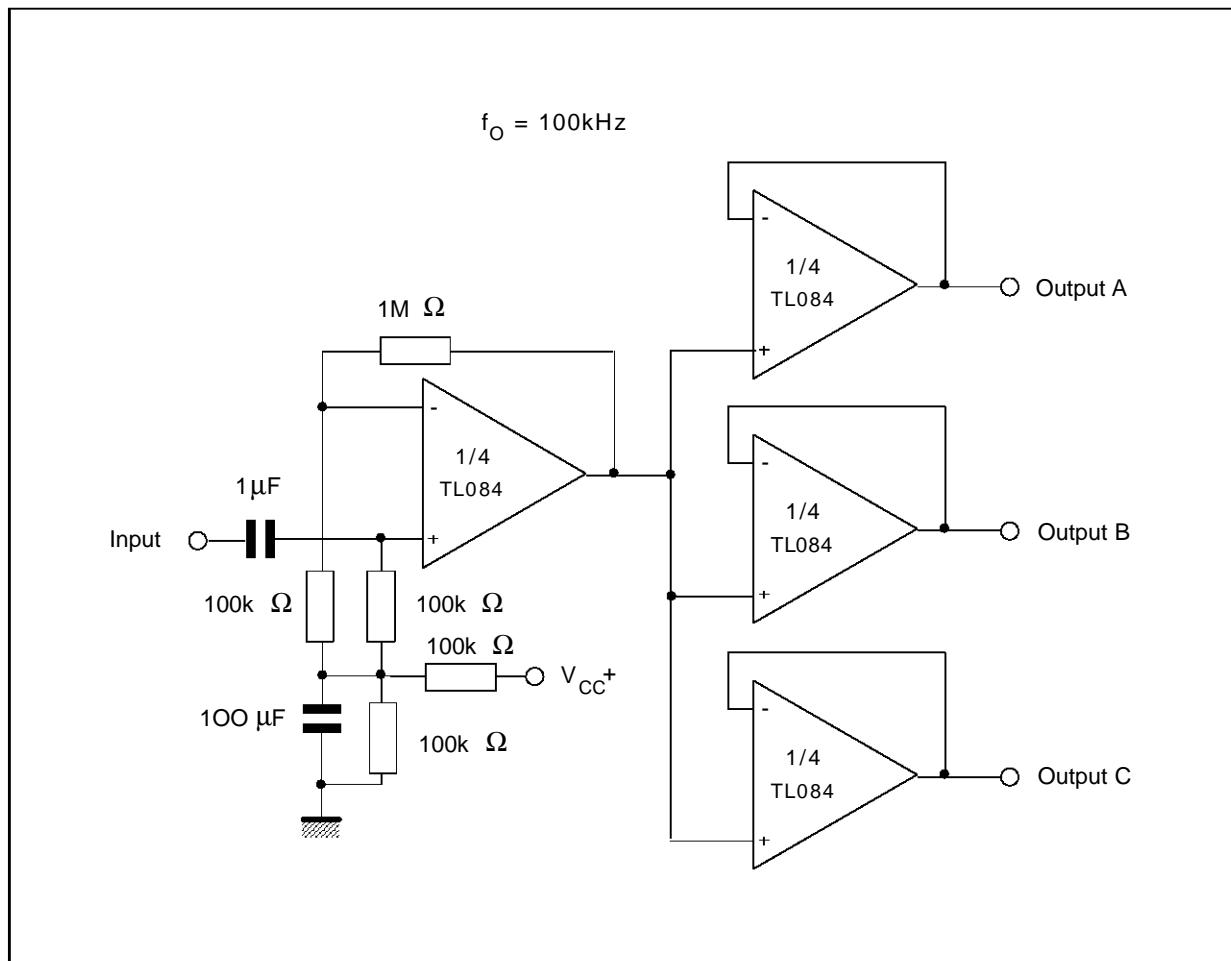


Figure 2 : Gain-of-10 Inverting Amplifier



TYPICAL APPLICATIONS

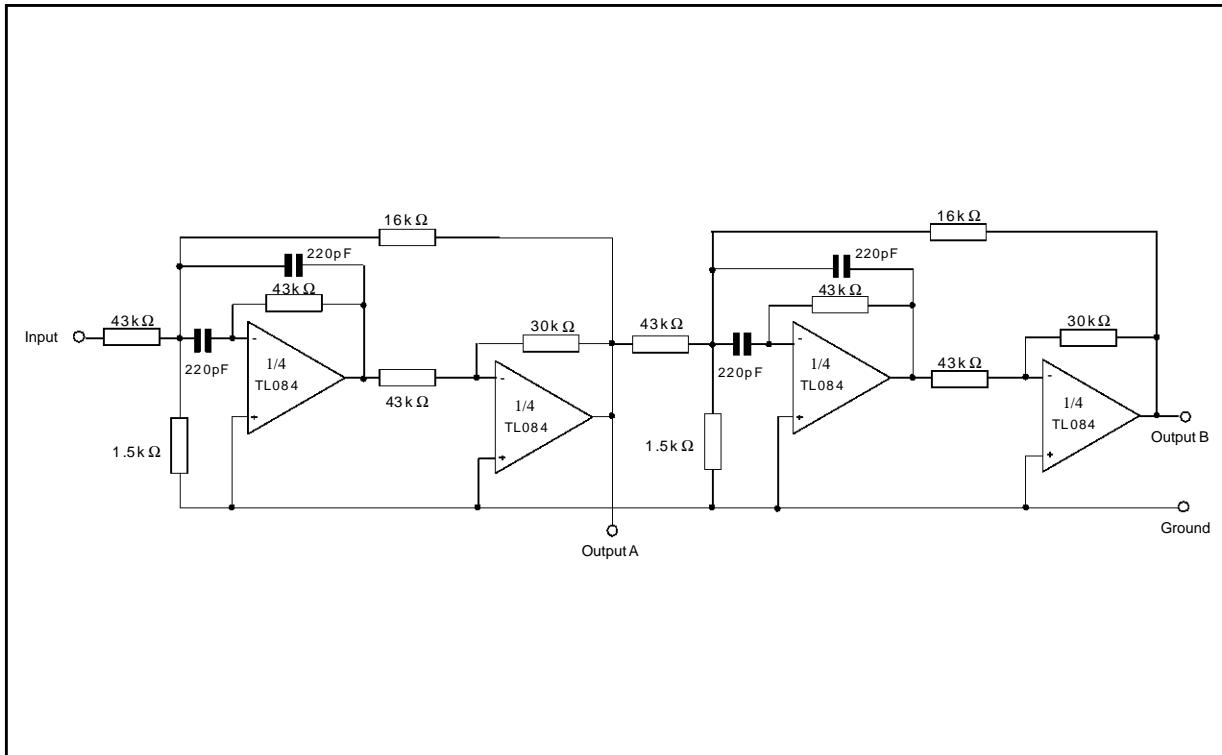
AUDIO DISTRIBUTION AMPLIFIER



TL084 - TL084A - TL084B

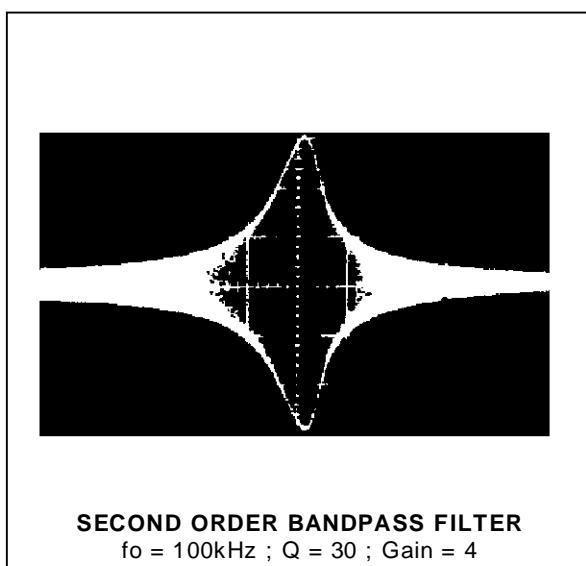
TYPICAL APPLICATIONS (continued)

POSITIVE FEEDBACK BANDPASS FILTER

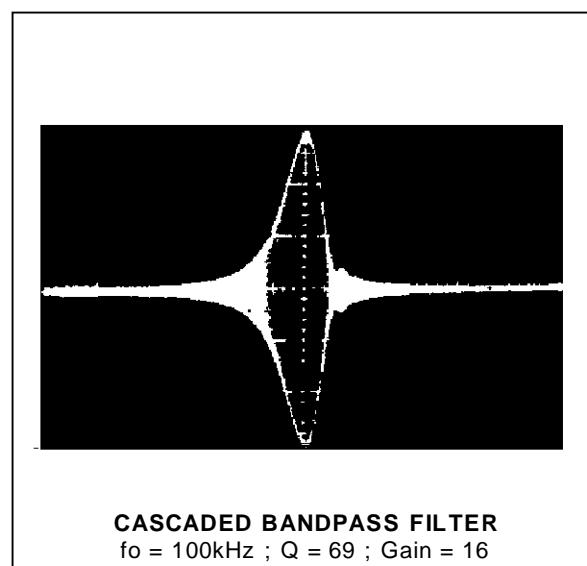


084-23.EPS

OUTPUT A

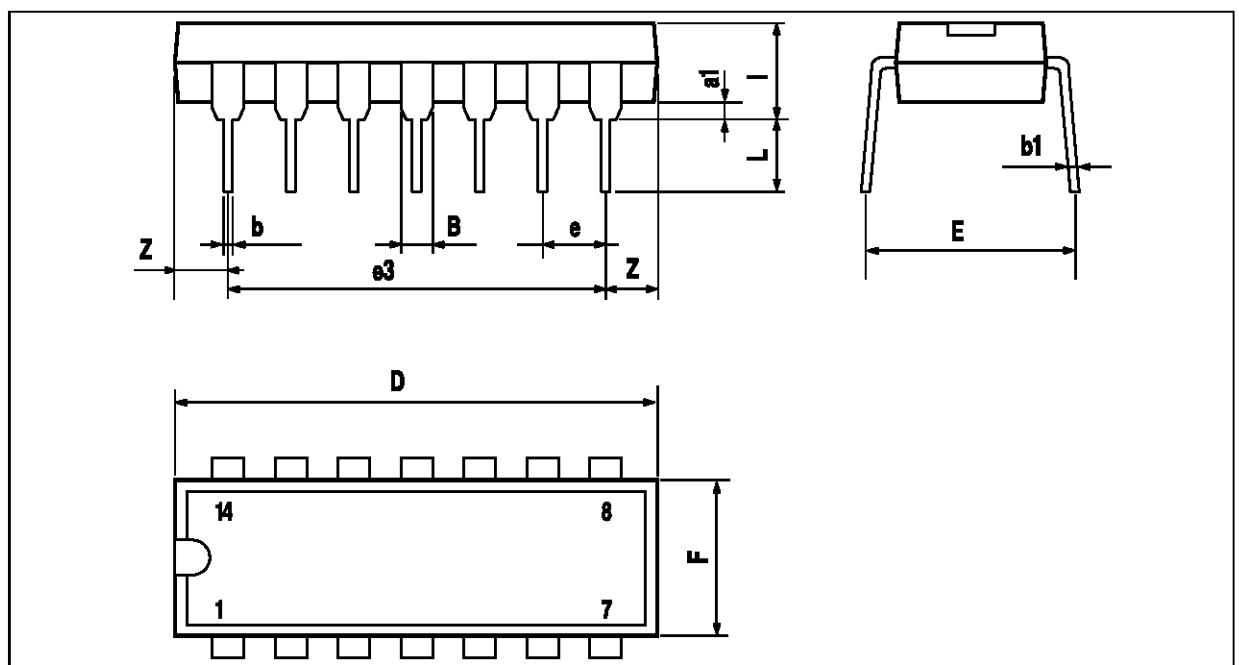


OUTPUT B



084-24.EPS

PACKAGE MECHANICAL DATA
14 PINS - PLASTIC DIP OR CERDIP



PNP-DIP14.EPS

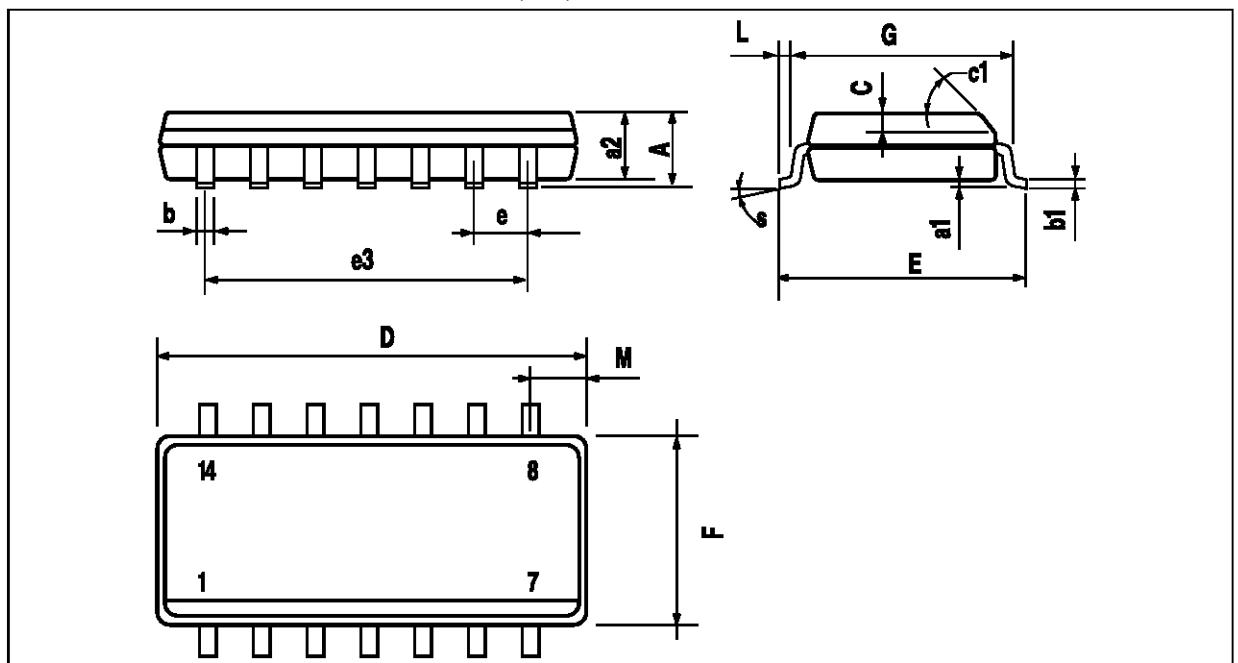
DIP14.TBL

Dimensions	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
a1	0.51			0.020		
B	1.39		1.65	0.055		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
e		2.54			0.100	
e3		15.24			0.600	
F			7.1			0.280
i			5.1			0.201
L		3.3			0.130	
Z	1.27		2.54	0.050		0.100

TL084 - TL084A - TL084B

PACKAGE MECHANICAL DATA

14 PINS - PLASTIC MICROPACKAGE (SO)



PLASTIC SO14-EPS

Dimensions	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A			1.75			0.069
a1	0.1		0.2	0.004		0.008
a2			1.6			0.063
b	0.35		0.46	0.014		0.018
b1	0.19		0.25	0.007		0.010
C		0.5			0.020	
c1	45° (typ.)					
D	8.55		8.75	0.336		0.334
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		7.62			0.300	
F	3.8		4.0	0.150		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.020		0.050
M			0.68			0.027
S	8° (max.)					

SO14-TBL

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